EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	70	257/314.ccls. and (SiC)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 07:10
L2	90	257/315.ccls. and (SiC)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 07:11
L3	117	257/314.ccls. and (SiC or (silicon near carbide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 07:12
L4	90	257/315.ccls. and (SiC)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 07:12
L5	144	257/315.ccls. and (SiC or (silicon near carbide))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 07:12
L8	1	(SiC and floating and gate and interface and control and first and second and insulat$3 and barrier and metal and semiconductor and quantum and well and group$1III and source and drain).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/07/20 07:39
L9	1	(SiC and floating and gate and first and second and insulat$3 and barrier and metal and semiconductor and well and group$1III and source and drain).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/07/20 07:43

L10	126	((jun near suda) or (hiroyuki near matsunami)).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/07/20 07:46
L11	1	((jun near suda) or (hiroyuki near matsunami)).in. and memory and SiC	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/07/20 07:46
L12	1	((jun near suda) or (hiroyuki near matsunami)).in. and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/07/20 07:46
L13	126	((jun near suda) or (hiroyuki near matsunami)).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/07/20 07:46
S1	1	"10565624"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 20:39
S2	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:07
S3	2	("5900648").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:10
S4	1268	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:15

S5	83939	AIN or (Aluminum near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:19
S6	155	S4 and S5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:19
S7	17	S6 and (AIN with thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:20
S8	7	S7 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:22
S9	22	S6 and (AIN same thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:24
S10	9	S9 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:24
S11	80	S6 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:28
S12	11	S11 and (AIN with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:30

S13	25	("3692700" | "4849797" | "5107315" | "5135885" | "5184199" | "5258631" | "5326992" | "5382822" | "5539217" | "5597744" | "5614749").PN. OR ("5900648").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/21 21:38
S14	43235	(AIN or (Aluminum near nitride) same ("SiO.sub.2" or oxide) same gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:46
S15	42515	(AIN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:46
S16	111	S4 and S15	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:47
S17	61	S16 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:47
S18	1628	(AIN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:49
S19	32	S4 and S18	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:49
S20	22	S19 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 21:49

S21	696	S18 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 22:01
S22	9117	(SiC or (silicon near carbide)) near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 22:04
S23	39	S21 and S22	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 22:04
S24	412	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 22:19
S25	125	S24 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/21 22:20
S26	1268	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 01:37
S27	42515	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 01:37
S28	111	S26 and S27	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 01:37

S29	61	S28 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 01:37
S30	4	S29 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 01:37
S31	901	(SiC or (silicon near carbide) with substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:29
S32	402	S31 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:30
S33	845	(SiC or (silicon near carbide) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:31
S34	381	S33 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:31
S35	40	((SiC or (silicon near carbide)) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:32
S36	15	S35 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:32

S37	84	((SiC or (silicon near carbide)) near substrate) and (EEPROM or (non-volatile near memory))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:36
S38	23	S37 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:36
S39	239	((SiC or (silicon near carbide)) near substrate) and Flash	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:37
S40	90	S39 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 02:38
S41	7	257/314.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 03:24
S42	105	257/76.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 03:25
S43	140	257/77.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 03:25
S44	22	257/410.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 03:25

S45	35	257/613.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 03:25
S46	3	257/629.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 03:25
S47	11	08/902098	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 03:42
S48	293	(AlN or (Aluminum near nitride)) same ("Al.sub.2O.sub.3" or (Aluminum near oxide)) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 05:21
S49	1268	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 05:21
S50	4	S48 and S49	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 05:21
S51	0	S50 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 05:21
S52	70	S48 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 05:23

S53	31536	(SiC or (silicon near carbide)) with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 05:23
S54	21	S48 and S53	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 05:23
S55	6	S54 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/12/22 05:23
S56	1	"10565624"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S57	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S58	2	("5900648").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S59	1381	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S60	88419	AlN or (Aluminum near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16

S61	171	S59 and S60	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S62	18	S61 and (AIN with thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S63	7	S62 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S64	26	S61 and (AIN same thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S65	9	S64 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S66	80	S61 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S67	11	S66 and (AIN with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S68	25	("3692700" | "4849797" | "5107315" | "5135885" | "5184199" | "5258631" | "5326992" | "5382822" | "5539217" | "5597744" | "5614749").PN. OR ("5900648").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/07/01 12:16

S69	45230	(AlN or (Aluminum near nitride) same ("SiO.sub.2" or oxide) same gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S70	44444	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S71	123	S59 and S70	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S72	61	S71 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S73	1768	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S74	33	S59 and S73	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S75	22	S74 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S76	696	S73 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16

S77	9814	(SiC or (silicon near carbide)) near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S78	39	S76 and S77	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S79	446	(AIN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S80	125	S79 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S81	1381	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S82	44444	(AIN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S83	123	S81 and S82	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S84	61	S83 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16

S85	4	S84 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S86	987	(SiC or (silicon near carbide) with substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S87	403	S86 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S88	928	(SiC or (silicon near carbide) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S89	382	S88 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S90	42	((SiC or (silicon near carbide)) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S91	15	S90 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S92	91	((SiC or (silicon near carbide)) near substrate) and (EEPROM or (non-volatile near memory))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16

S93	23	S92 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S94	266	((SiC or (silicon near carbide)) near substrate) and Flash	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S95	90	S94 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S96	7	257/314.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S97	116	257/76.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S98	151	257/77.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S99	24	257/410.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S100	36	257/613.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16

S101	3	257/629.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S102	11	08/902098	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S103	319	(AlN or (Aluminum near nitride)) same ("Al.sub.2O.sub.3" or (Aluminum near oxide)) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S104	1381	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S105	4	S103 and S104	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S106	0	S105 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S107	70	S103 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S108	33799	(SiC or (silicon near carbide)) with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16

S109	24	S103 and S108	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S110	6	S109 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 12:16
S111	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/01 21:04
S112	1	"10565624"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S113	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S114	2	("5900648").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S115	1384	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S116	88506	AlN or (Aluminum near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23

S117	171	S115 and S116	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S118	18	S117 and (AIN with thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S119	7	S118 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S120	26	S117 and (AIN same thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S121	9	S120 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S122	80	S117 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S123	11	S122 and (AIN with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S124	25	("3692700" | "4849797" | "5107315" | "5135885" | "5184199" | "5258631" | "5326992" | "5382822" | "5539217" | "5597744" | "5614749").PN. OR ("5900648").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/07/02 10:23

S125	45274	(AlN or (Aluminum near nitride) same ("SiO.sub.2" or oxide) same gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S126	44488	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S127	123	S115 and S126	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S128	61	S127 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S129	1772	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S130	33	S115 and S129	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S131	22	S130 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S132	696	S129 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23

S133	9836	(SiC or (silicon near carbide)) near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S134	39	S132 and S133	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S135	447	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S136	125	S135 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S137	1384	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S138	44488	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S139	123	S137 and S138	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S140	61	S139 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23

S141	4	S140 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S142	989	(SiC or (silicon near carbide) with substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S143	403	S142 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S144	930	(SiC or (silicon near carbide) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S145	382	S144 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S146	42	((SiC or (silicon near carbide)) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S147	15	S146 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S148	91	((SiC or (silicon near carbide)) near substrate) and (EEPROM or (non-volatile near memory))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23

S149	23	S148 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S150	266	((SiC or (silicon near carbide)) near substrate) and Flash	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S151	90	S150 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S152	7	257/314.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S153	116	257/76.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S154	151	257/77.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S155	24	257/410.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S156	36	257/613.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23

S157	3	257/629.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S158	11	08/902098	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S159	319	(AlN or (Aluminum near nitride)) same ("Al.sub.2O. sub.3" or (Aluminum near oxide)) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S160	1384	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S161	4	S159 and S160	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S162	0	S161 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S163	70	S159 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S164	33864	(SiC or (silicon near carbide)) with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23

S165	24	S159 and S164	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S166	6	S165 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S167	1	"10565624"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S168	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S169	2	("5900648").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S170	1384	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S171	88506	AlN or (Aluminum near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S172	171	S170 and S171	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23

S173	18	S172 and (AIN with thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S174	7	S173 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S175	26	S172 and (AIN same thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S176	9	S175 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S177	80	S172 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S178	11	S177 and (AIN with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S179	25	("3692700" | "4849797" | "5107315" | "5135885" | "5184199" | "5258631" | "5326992" | "5382822" | "5539217" | "5597744" | "5614749").PN. OR ("5900648").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/07/02 10:23
S180	45274	(AIN or (Aluminum near nitride) same ("SiO.sub.2" or oxide) same gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23

S181	44488	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S182	123	S170 and S181	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S183	61	S182 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S184	1772	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S185	33	S170 and S184	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S186	22	S185 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S187	696	S184 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S188	9836	(SiC or (silicon near carbide)) near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23

S189	39	S187 and S188	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S190	447	(AIN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S191	125	S190 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S192	1384	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S193	44488	(AIN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S194	123	S192 and S193	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S195	61	S194 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S196	4	S195 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23

S197	989	(SiC or (silicon near carbide) with substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S198	403	S197 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S199	930	(SiC or (silicon near carbide) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S200	382	S199 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S201	42	((SiC or (silicon near carbide)) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S202	15	S201 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S203	91	((SiC or (silicon near carbide)) near substrate) and (EEPROM or (non-volatile near memory))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S204	23	S203 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23

S205	266	((SiC or (silicon near carbide)) near substrate) and Flash	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S206	90	S205 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S207	7	257/314.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S208	116	257/76.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S209	151	257/77.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S210	24	257/410.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S211	36	257/613.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S212	3	257/629.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23

S213	11	08/902098	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S214	319	(AIN or (Aluminum near nitride)) same ("Al.sub.2O.sub.3" or (Aluminum near oxide)) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S215	1384	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S216	4	S214 and S215	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S217	0	S216 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S218	70	S214 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S219	33864	(SiC or (silicon near carbide)) with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S220	24	S214 and S219	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23

S221	6	S220 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S222	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/02 10:23
S223	1	"10565624"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S224	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S225	2	("5900648").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S226	1384	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S227	88506	AlN or (Aluminum near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S228	171	S226 and S227	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24

S229	18	S228 and (AlN with thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S230	7	S229 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S231	26	S228 and (AlN same thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S232	9	S231 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S233	80	S228 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S234	11	S233 and (AlN with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S235	25	("3692700" | "4849797" | "5107315" | "5135885" | "5184199" | "5258631" | "5326992" | "5382822" | "5539217" | "5597744" | "5614749").PN. OR ("5900648").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/07/05 22:24
S236	45274	(AlN or (Aluminum near nitride) same ("SiO.sub.2" or oxide) same gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24

S237	44488	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S238	123	S226 and S237	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S239	61	S238 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S240	1772	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S241	33	S226 and S240	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S242	22	S241 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S243	696	S240 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S244	9836	(SiC or (silicon near carbide)) near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24

S245	39	S243 and S244	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S246	447	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S247	125	S246 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S248	1384	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S249	44488	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S250	123	S248 and S249	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S251	61	S250 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S252	4	S251 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24

S253	989	(SiC or (silicon near carbide) with substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S254	403	S253 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S255	930	(SiC or (silicon near carbide) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S256	382	S255 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S257	42	((SiC or (silicon near carbide)) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S258	15	S257 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S259	91	((SiC or (silicon near carbide)) near substrate) and (EEPROM or (non-volatile near memory))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S260	23	S259 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24

S261	266	((SiC or (silicon near carbide)) near substrate) and Flash	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S262	90	S261 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S263	7	257/314.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S264	116	257/76.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S265	151	257/77.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:24
S266	24	257/410.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S267	36	257/613.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S268	3	257/629.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S269	11	08/902098	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S270	319	(AlN or (Aluminum near nitride)) same ("Al.sub.2O. sub.3" or (Aluminum near oxide)) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S271	1384	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S272	4	S270 and S271	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S273	0	S272 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S274	70	S270 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S275	33864	(SiC or (silicon near carbide)) with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S276	24	S270 and S275	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S277	6	S276 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S278	1	"10565624"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S279	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S280	2	("5900648").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S281	1384	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S282	88506	AlN or (Aluminum near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S283	171	S281 and S282	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S284	18	S283 and (AlN with thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S285	7	S284 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S286	26	S283 and (AIN same thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S287	9	S286 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S288	80	S283 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S289	11	S288 and (AIN with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S290	25	("3692700" | "4849797" | "5107315" | "5135885" | "5184199" | "5258631" | "5326992" | "5382822" | "5539217" | "5597744" | "5614749").PN. OR ("5900648").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/07/05 22:25
S291	45274	(AIN or (Aluminum near nitride) same ("SiO.sub.2" or oxide) same gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S292	44488	(AIN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S293	123	S281 and S292	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S294	61	S293 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S295	1772	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S296	33	S281 and S295	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S297	22	S296 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S298	696	S295 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S299	9836	(SiC or (silicon near carbide)) near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S300	39	S298 and S299	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S301	447	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S302	125	S301 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S303	1384	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S304	44488	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S305	123	S303 and S304	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S306	61	S305 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S307	4	S306 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S308	989	(SiC or (silicon near carbide) with substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S309	403	S308 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S310	930	(SiC or (silicon near carbide) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S311	382	S310 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S312	42	((SiC or (silicon near carbide)) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S313	15	S312 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S314	91	((SiC or (silicon near carbide)) near substrate) and (EEPROM or (non-volatile near memory))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S315	23	S314 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S316	266	((SiC or (silicon near carbide)) near substrate) and Flash	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S317	90	S316 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S318	7	257/314.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S319	116	257/76.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S320	151	257/77.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S321	24	257/410.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S322	36	257/613.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S323	3	257/629.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S324	11	08/902098	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S325	319	(AIN or (Aluminum near nitride)) same ("Al.sub.2O.sub.3" or (Aluminum near oxide)) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S326	1384	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S327	4	S325 and S326	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S328	0	S327 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S329	70	S325 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S330	33864	(SiC or (silicon near carbide)) with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S331	24	S325 and S330	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S332	6	S331 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S333	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S334	1	"10565624"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S335	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S336	2	("5900648").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S337	1384	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S338	88506	AlN or (Aluminum near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S339	171	S337 and S338	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S340	18	S339 and (AlN with thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S341	7	S340 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S342	26	S339 and (AlN same thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S343	9	S342 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S344	80	S339 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S345	11	S344 and (AlN with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S346	25	("3692700" | "4849797" | "5107315" | "5135885" | "5184199" | "5258631" | "5326992" | "5382822" | "5539217" | "5597744" | "5614749").PN. OR ("5900648").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/07/05 22:25
S347	45274	(AlN or (Aluminum near nitride) same ("SiO.sub.2" or oxide) same gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S348	44488	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S349	123	S337 and S348	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S350	61	S349 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S351	1772	(AIN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S352	33	S337 and S351	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S353	22	S352 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S354	696	S351 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S355	9836	(SiC or (silicon near carbide)) near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S356	39	S354 and S355	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S357	447	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S358	125	S357 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S359	1384	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S360	44488	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S361	123	S359 and S360	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S362	61	S361 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S363	4	S362 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S364	989	(SiC or (silicon near carbide) with substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S365	403	S364 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S366	930	(SiC or (silicon near carbide) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S367	382	S366 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S368	42	((SiC or (silicon near carbide)) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S369	15	S368 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S370	91	((SiC or (silicon near carbide)) near substrate) and (EEPROM or (non-volatile near memory))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S371	23	S370 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S372	266	((SiC or (silicon near carbide)) near substrate) and Flash	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S373	90	S372 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S374	7	257/314.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S375	116	257/76.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S376	151	257/77.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S377	24	257/410.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S378	36	257/613.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S379	3	257/629.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S380	11	08/902098	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S381	319	(AlN or (Aluminum near nitride)) same ("Al.sub.2O.sub.3" or (Aluminum near oxide)) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S382	1384	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S383	4	S381 and S382	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S384	0	S383 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S385	70	S381 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S386	33864	(SiC or (silicon near carbide)) with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S387	24	S381 and S386	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S388	6	S387 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S389	1	"10565624"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S390	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S391	2	("5900648").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S392	1384	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S393	88506	AlN or (Aluminum near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S394	171	S392 and S393	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S395	18	S394 and (AlN with thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S396	7	S395 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S397	26	S394 and (AlN same thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S398	9	S397 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S399	80	S394 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S400	11	S399 and (AlN with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S401	25	("3692700" | "4849797" | "5107315" | "5135885" | "5184199" | "5258631" | "5326992" | "5382822" | "5539217" | "5597744" | "5614749").PN. OR ("5900648").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/07/05 22:25
S402	45274	(AlN or (Aluminum near nitride) same ("SiO.sub.2" or oxide) same gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S403	44488	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S404	123	S392 and S403	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S405	61	S404 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S406	1772	(AIN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S407	33	S392 and S406	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S408	22	S407 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S409	696	S406 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S410	9836	(SiC or (silicon near carbide)) near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S411	39	S409 and S410	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S412	447	(AIN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S413	125	S412 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S414	1384	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S415	44488	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S416	123	S414 and S415	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S417	61	S416 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S418	4	S417 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S419	989	(SiC or (silicon near carbide) with substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S420	403	S419 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S421	930	(SiC or (silicon near carbide) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S422	382	S421 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S423	42	((SiC or (silicon near carbide)) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S424	15	S423 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S425	91	((SiC or (silicon near carbide)) near substrate) and (EEPROM or (non-volatile near memory))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S426	23	S425 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S427	266	((SiC or (silicon near carbide)) near substrate) and Flash	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S428	90	S427 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S429	7	257/314.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S430	116	257/76.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S431	151	257/77.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S432	24	257/410.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S433	36	257/613.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S434	3	257/629.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S435	11	08/902098	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S436	319	(AlN or (Aluminum near nitride)) same ("Al.sub.2O.sub.3" or (Aluminum near oxide)) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S437	1384	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S438	4	S436 and S437	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S439	0	S438 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S440	70	S436 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S441	33864	(SiC or (silicon near carbide)) with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S442	24	S436 and S441	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S443	6	S442 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25
S444	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:25

S445	187	(AlN or (Aluminum near nitride) or Group$lll) near interface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:44
S446	5	S226 and S445	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:44
S447	2	S446 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/05 22:45
S448	18519	(SiC or (silicon near carbide) with substrate) and (memory storage)	US-PGPUB; USPAT	OR	ON	2009/07/20 03:08
S449	98	S448 and (floating near gate) with (GaN or (group $1lll near nitride))	US-PGPUB; USPAT	OR	ON	2009/07/20 03:10
S450	38	S449 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 03:10
S451	50	S448 and (gate same (GaN or (group$1lll near nitride)) same (AlN or (group$1lll near nitride)))	US-PGPUB; USPAT	OR	ON	2009/07/20 03:39
S452	25	S451 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 03:41
S456	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 03:59
S457	88870	AlN or (Aluminum near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 03:59

S458	172	S456 and S457	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 03:59
S461	26	S458 and (AlN same thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 03:59
S466	45423	(AlN or (Aluminum near nitride) same ("SiO.sub.2" or oxide) same gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 03:59
S467	44632	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 03:59
S468	124	S456 and S467	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 03:59
S470	1784	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 03:59
S471	34	S456 and S470	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 03:59
S472	1	"10565624"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S473	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S474	2	("5900648").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S475	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S476	88870	AIN or (Aluminum near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S477	172	S475 and S476	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S478	18	S477 and (AIN with thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S479	7	S478 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S480	26	S477 and (AIN same thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S481	9	S480 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S482	80	S477 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S483	11	S482 and (AIN with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S484	25	("3692700" | "4849797" | "5107315" | "5135885" | "5184199" | "5258631" | "5326992" | "5382822" | "5539217" | "5597744" | "5614749").PN. OR ("5900648").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/07/20 04:57
S485	45423	(AIN or (Aluminum near nitride) same ("SiO.sub.2" or oxide) same gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S486	44632	(AIN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S487	124	S475 and S486	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S488	61	S487 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S489	1784	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S490	34	S475 and S489	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S491	22	S490 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S492	696	S489 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S493	9889	(SiC or (silicon near carbide)) near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S494	39	S492 and S493	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S495	448	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S496	125	S495 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S497	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S498	44632	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S499	124	S497 and S498	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S500	61	S499 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S501	4	S500 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S502	993	(SiC or (silicon near carbide) with substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S503	403	S502 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S504	934	(SiC or (silicon near carbide) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S505	382	S504 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S506	42	((SiC or (silicon near carbide)) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S507	15	S506 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S508	92	((SiC or (silicon near carbide)) near substrate) and (EEPROM or (non-volatile near memory))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S509	23	S508 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S510	267	((SiC or (silicon near carbide)) near substrate) and Flash	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S511	90	S510 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S512	7	257/314.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S513	116	257/76.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S514	153	257/77.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S515	24	257/410.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S516	36	257/613.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S517	3	257/629.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S518	11	08/902098	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S519	320	(AlN or (Aluminum near nitride)) same ("Al.sub.2O.sub.3" or (Aluminum near oxide)) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S520	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S521	4	S519 and S520	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S522	0	S521 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S523	70	S519 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S524	34026	(SiC or (silicon near carbide)) with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S525	24	S519 and S524	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S526	6	S525 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S527	1	"10565624"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S528	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S529	2	("5900648").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S530	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S531	88870	AlN or (Aluminum near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S532	172	S530 and S531	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S533	18	S532 and (AlN with thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S534	7	S533 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S535	26	S532 and (AlN same thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S536	9	S535 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S537	80	S532 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S538	11	S537 and (AIN with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S539	25	("3692700" | "4849797" | "5107315" | "5135885" | "5184199" | "5258631" | "5326992" | "5382822" | "5539217" | "5597744" | "5614749").PN. OR ("5900648").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/07/20 04:57
S540	45423	(AIN or (Aluminum near nitride) same ("SiO.sub.2" or oxide) same gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S541	44632	(AIN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S542	124	S530 and S541	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S543	61	S542 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S544	1784	(AIN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S545	34	S530 and S544	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S546	22	S545 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S547	696	S544 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S548	9889	(SiC or (silicon near carbide)) near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S549	39	S547 and S548	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S550	448	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S551	125	S550 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S552	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S553	44632	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S554	124	S552 and S553	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S555	61	S554 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S556	4	S555 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S557	993	(SiC or (silicon near carbide) with substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S558	403	S557 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S559	934	(SiC or (silicon near carbide) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S560	382	S559 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S561	42	((SiC or (silicon near carbide)) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S562	15	S561 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S563	92	((SiC or (silicon near carbide)) near substrate) and (EEPROM or (non-volatile near memory))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S564	23	S563 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S565	267	((SiC or (silicon near carbide)) near substrate) and Flash	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S566	90	S565 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S567	7	257/314.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S568	116	257/76.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S569	153	257/77.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S570	24	257/410.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S571	36	257/613.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S572	3	257/629.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S573	11	08/902098	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S574	320	(AlN or (Aluminum near nitride)) same ("Al.sub.2O.sub.3" or (Aluminum near oxide)) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S575	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S576	4	S574 and S575	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S577	0	S576 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S578	70	S574 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S579	34026	(SiC or (silicon near carbide)) with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S580	24	S574 and S579	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S581	6	S580 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S582	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S583	1	"10565624"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S584	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S585	2	("5900648").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S586	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S587	88870	AIN or (Aluminum near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S588	172	S586 and S587	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S589	18	S588 and (AIN with thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S590	7	S589 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S591	26	S588 and (AIN same thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S592	9	S591 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S593	80	S588 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S594	11	S593 and (AlN with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S595	25	("3692700" | "4849797" | "5107315" | "5135885" | "5184199" | "5258631" | "5326992" | "5382822" | "5539217" | "5597744" | "5614749").PN. OR ("5900648").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/07/20 04:57
S596	45423	(AlN or (Aluminum near nitride) same ("SiO.sub.2" or oxide) same gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S597	44632	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S598	124	S586 and S597	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S599	61	S598 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S600	1784	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S601	34	S586 and S600	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S602	22	S601 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S603	696	S600 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S604	9889	(SiC or (silicon near carbide)) near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S605	39	S603 and S604	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S606	448	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S607	125	S606 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S608	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S609	44632	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S610	124	S608 and S609	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S611	61	S610 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S612	4	S611 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S613	993	(SiC or (silicon near carbide) with substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S614	403	S613 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S615	934	(SiC or (silicon near carbide) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S616	382	S615 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S617	42	((SiC or (silicon near carbide)) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S618	15	S617 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S619	92	((SiC or (silicon near carbide)) near substrate) and (EEPROM or (non-volatile near memory))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S620	23	S619 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S621	267	((SiC or (silicon near carbide)) near substrate) and Flash	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S622	90	S621 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S623	7	257/314.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S624	116	257/76.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S625	153	257/77.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S626	24	257/410.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S627	36	257/613.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S628	3	257/629.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S629	11	08/902098	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S630	320	(AlN or (Aluminum near nitride)) same ("Al.sub.2O.sub.3" or (Aluminum near oxide)) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S631	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S632	4	S630 and S631	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S633	0	S632 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S634	70	S630 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S635	34026	(SiC or (silicon near carbide)) with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S636	24	S630 and S635	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S637	6	S636 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S638	1	"10565624"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S639	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S640	2	("5900648").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S641	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S642	88870	AlN or (Aluminum near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S643	172	S641 and S642	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S644	18	S643 and (AlN with thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S645	7	S644 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S646	26	S643 and (AlN same thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S647	9	S646 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S648	80	S643 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S649	11	S648 and (AIN with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S650	25	("3692700" | "4849797" | "5107315" | "5135885" | "5184199" | "5258631" | "5326992" | "5382822" | "5539217" | "5597744" | "5614749").PN. OR ("5900648").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/07/20 04:57
S651	45423	(AIN or (Aluminum near nitride) same ("SiO.sub.2" or oxide) same gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S652	44632	(AIN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S653	124	S641 and S652	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S654	61	S653 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S655	1784	(AIN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S656	34	S641 and S655	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S657	22	S656 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S658	696	S655 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S659	9889	(SiC or (silicon near carbide)) near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S660	39	S658 and S659	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S661	448	(AIN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S662	125	S661 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S663	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S664	44632	(AIN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S665	124	S663 and S664	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S666	61	S665 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S667	4	S666 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S668	993	(SiC or (silicon near carbide) with substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S669	403	S668 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S670	934	(SiC or (silicon near carbide) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S671	382	S670 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S672	42	((SiC or (silicon near carbide)) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S673	15	S672 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S674	92	((SiC or (silicon near carbide)) near substrate) and (EEPROM or (non-volatile near memory))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S675	23	S674 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S676	267	((SiC or (silicon near carbide)) near substrate) and Flash	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S677	90	S676 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S678	7	257/314.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S679	116	257/76.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S680	153	257/77.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S681	24	257/410.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S682	36	257/613.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S683	3	257/629.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S684	11	08/902098	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S685	320	(AlN or (Aluminum near nitride)) same ("Al.sub.2O.sub.3" or (Aluminum near oxide)) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S686	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S687	4	S685 and S686	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S688	0	S687 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S689	70	S685 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S690	34026	(SiC or (silicon near carbide)) with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S691	24	S685 and S690	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S692	6	S691 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S693	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S694	1	"10565624"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S695	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S696	2	("5900648").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S697	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S698	88870	AlN or (Aluminum near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S699	172	S697 and S698	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S700	18	S699 and (AlN with thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S701	7	S700 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S702	26	S699 and (AlN same thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S703	9	S702 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S704	80	S699 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57

S705	11	S704 and (AIN with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:57
S706	25	("3692700" | "4849797" | "5107315" | "5135885" | "5184199" | "5258631" | "5326992" | "5382822" | "5539217" | "5597744" | "5614749").PN. OR ("5900648").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/07/20 04:57
S707	45423	(AIN or (Aluminum near nitride) same ("SiO.sub.2" or oxide) same gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S708	44632	(AIN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S709	124	S697 and S708	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S710	61	S709 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S711	1784	(AIN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S712	34	S697 and S711	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S713	22	S712 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S714	696	S711 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S715	9889	(SiC or (silicon near carbide)) near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S716	39	S714 and S715	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S717	448	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S718	125	S717 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S719	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S720	44632	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S721	124	S719 and S720	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S722	61	S721 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S723	4	S722 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S724	993	(SiC or (silicon near carbide) with substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S725	403	S724 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S726	934	(SiC or (silicon near carbide) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S727	382	S726 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S728	42	((SiC or (silicon near carbide)) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S729	15	S728 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S730	92	((SiC or (silicon near carbide)) near substrate) and (EEPROM or (non-volatile near memory))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S731	23	S730 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S732	267	((SiC or (silicon near carbide)) near substrate) and Flash	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S733	90	S732 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S734	7	257/314.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S735	116	257/76.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S736	153	257/77.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S737	24	257/410.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S738	36	257/613.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S739	3	257/629.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S740	11	08/902098	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S741	320	(AlN or (Aluminum near nitride)) same ("Al.sub.2O.sub.3" or (Aluminum near oxide)) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S742	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S743	4	S741 and S742	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S744	0	S743 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S745	70	S741 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S746	34026	(SiC or (silicon near carbide)) with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S747	24	S741 and S746	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S748	6	S747 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S749	1	"10565624"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S750	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S751	2	("5900648").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S752	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S753	88870	AIN or (Aluminum near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S754	172	S752 and S753	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S755	18	S754 and (AIN with thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S756	7	S755 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S757	26	S754 and (AIN same thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S758	9	S757 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S759	80	S754 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S760	11	S759 and (AIN with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S761	25	("3692700" | "4849797" | "5107315" | "5135885" | "5184199" | "5258631" | "5326992" | "5382822" | "5539217" | "5597744" | "5614749").PN. OR ("5900648").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/07/20 04:58
S762	45423	(AIN or (Aluminum near nitride) same ("SiO.sub.2" or oxide) same gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S763	44632	(AIN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S764	124	S752 and S763	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S765	61	S764 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S766	1784	(AIN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S767	34	S752 and S766	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S768	22	S767 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S769	696	S766 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S770	9889	(SiC or (silicon near carbide)) near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S771	39	S769 and S770	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S772	448	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S773	125	S772 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S774	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S775	44632	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S776	124	S774 and S775	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S777	61	S776 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S778	4	S777 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S779	993	(SiC or (silicon near carbide) with substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S780	403	S779 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S781	934	(SiC or (silicon near carbide) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S782	382	S781 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S783	42	((SiC or (silicon near carbide)) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S784	15	S783 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S785	92	((SiC or (silicon near carbide)) near substrate) and (EEPROM or (non-volatile near memory))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S786	23	S785 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S787	267	((SiC or (silicon near carbide)) near substrate) and Flash	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S788	90	S787 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S789	7	257/314.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S790	116	257/76.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S791	153	257/77.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S792	24	257/410.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S793	36	257/613.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S794	3	257/629.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S795	11	08/902098	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S796	320	(AlN or (Aluminum near nitride)) same ("Al.sub.2O.sub.3" or (Aluminum near oxide)) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S797	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S798	4	S796 and S797	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S799	0	S798 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S800	70	S796 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S801	34026	(SiC or (silicon near carbide)) with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S802	24	S796 and S801	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S803	6	S802 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S804	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S805	1	"10565624"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S806	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S807	2	("5900648").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S808	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S809	88870	AIN or (Aluminum near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S810	172	S808 and S809	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S811	18	S810 and (AIN with thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S812	7	S811 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S813	26	S810 and (AIN same thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S814	9	S813 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S815	80	S810 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S816	11	S815 and (AIN with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S817	25	("3692700" | "4849797" | "5107315" | "5135885" | "5184199" | "5258631" | "5326992" | "5382822" | "5539217" | "5597744" | "5614749").PN. OR ("5900648").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/07/20 04:58
S818	45423	(AlN or (Aluminum near nitride) same ("SiO.sub.2" or oxide) same gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S819	44632	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S820	124	S808 and S819	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S821	61	S820 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S822	1784	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S823	34	S808 and S822	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S824	22	S823 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S825	696	S822 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S826	9889	(SiC or (silicon near carbide)) near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S827	39	S825 and S826	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S828	448	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S829	125	S828 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S830	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S831	44632	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S832	124	S830 and S831	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S833	61	S832 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S834	4	S833 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S835	993	(SiC or (silicon near carbide) with substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S836	403	S835 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S837	934	(SiC or (silicon near carbide) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S838	382	S837 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S839	42	((SiC or (silicon near carbide)) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S840	15	S839 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S841	92	((SiC or (silicon near carbide)) near substrate) and (EEPROM or (non-volatile near memory))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S842	23	S841 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S843	267	((SiC or (silicon near carbide)) near substrate) and Flash	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S844	90	S843 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S845	7	257/314.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S846	116	257/76.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S847	153	257/77.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S848	24	257/410.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S849	36	257/613.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S850	3	257/629.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S851	11	08/902098	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S852	320	(AlN or (Aluminum near nitride)) same ("Al.sub.2O.sub.3" or (Aluminum near oxide)) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S853	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S854	4	S852 and S853	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S855	0	S854 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S856	70	S852 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S857	34026	(SiC or (silicon near carbide)) with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S858	24	S852 and S857	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S859	6	S858 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S860	1	"10565624"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S861	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S862	2	("5900648").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S863	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S864	88870	AlN or (Aluminum near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S865	172	S863 and S864	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S866	18	S865 and (AIN with thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S867	7	S866 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S868	26	S865 and (AIN same thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S869	9	S868 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S870	80	S865 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S871	11	S870 and (AIN with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S872	25	("3692700" | "4849797" | "5107315" | "5135885" | "5184199" | "5258631" | "5326992" | "5382822" | "5539217" | "5597744" | "5614749").PN. OR ("5900648").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2009/07/20 04:58

S873	45423	(AlN or (Aluminum near nitride) same ("SiO.sub.2" or oxide) same gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S874	44632	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S875	124	S863 and S874	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S876	61	S875 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S877	1784	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S878	34	S863 and S877	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S879	22	S878 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S880	696	S877 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S881	9889	(SiC or (silicon near carbide)) near substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S882	39	S880 and S881	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S883	448	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S884	125	S883 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S885	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S886	44632	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S887	124	S885 and S886	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S888	61	S887 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S889	4	S888 and memory	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S890	993	(SiC or (silicon near carbide) with substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S891	403	S890 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S892	934	(SiC or (silicon near carbide) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S893	382	S892 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S894	42	((SiC or (silicon near carbide)) near substrate) and (non-volatile near memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S895	15	S894 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S896	92	((SiC or (silicon near carbide)) near substrate) and (EEPROM or (non-volatile near memory))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S897	23	S896 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S898	267	((SiC or (silicon near carbide)) near substrate) and Flash	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S899	90	S898 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S900	7	257/314.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S901	116	257/76.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S902	153	257/77.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S903	24	257/410.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S904	36	257/613.ccls. and (SiC) and AIN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S905	3	257/629.ccls. and (SiC) and AlN	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S906	11	08/902098	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S907	320	(AlN or (Aluminum near nitride)) same ("Al.sub.2O.sub.3" or (Aluminum near oxide)) same (gate near (insulator dielectric))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S908	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S909	4	S907 and S908	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S910	0	S909 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S911	70	S907 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S912	34026	(SiC or (silicon near carbide)) with substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S913	24	S907 and S912	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S914	6	S913 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S915	2	"2000150792"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S916	189	(AIN or (Aluminum near nitride) or Group$III) near interface	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S917	5	S697 and S916	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S918	2	S917 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S919	18519	(SiC or (silicon near carbide) with substrate) and (memory storage)	US-PGPUB; USPAT	OR	ON	2009/07/20 04:58
S920	98	S919 and (floating near gate) with (GaN or (group $1III near nitride))	US-PGPUB; USPAT	OR	ON	2009/07/20 04:58
S921	38	S920 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S922	50	S919 and (gate same (GaN or (group$1III near nitride)) same (AIN or (group$1III near nitride)))	US-PGPUB; USPAT	OR	ON	2009/07/20 04:58

S923	25	S922 and @ad<"20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S924	1392	(SiC or (silicon near carbide)) with (MISFET MOSFET)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S925	88870	AlN or (Aluminum near nitride)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S926	172	S924 and S925	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S927	26	S926 and (AlN same thickness)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S928	45423	(AlN or (Aluminum near nitride) same ("SiO.sub.2" or oxide) same gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S929	44632	(AlN or (Aluminum near nitride) with ("SiO.sub.2" or oxide) with gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S930	124	S924 and S929	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58

S931	1784	(AlN or (Aluminum near nitride)) same ("SiO.sub.2" or oxide) same gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S932	34	S924 and S931	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 04:58
S933	1	257/e21.063.ccls. and (gate same (GaN or (group $1III near nitride)) same (AlN or (group$1III near nitride)))	US-PGPUB; USPAT	OR	ON	2009/07/20 05:15
S934	102	257/e21.063.ccls.	US-PGPUB; USPAT	OR	ON	2009/07/20 05:15
S935	60	S934 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 05:18
S936	2153	257/e29.129.ccls.	US-PGPUB; USPAT	OR	ON	2009/07/20 05:25
S937	60	S935 and @ad< "20030728"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 05:26
S938	31	S935 and @ad< "20030728" and (Sic near substrate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/07/20 05:26

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